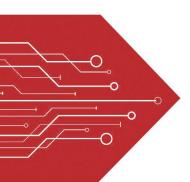
MSKSEMI















ESD

TVS

TSS

MOV

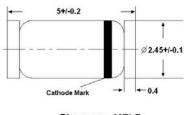
GDT

PLED

Broduct data sheet

for use in stabilizing and clipping circuits with high power rating. Standard Zener voltage tolerance is $\pm 10\%$. Add suffix "A" for $\pm 5\%$ tolerance and suffix "B" for $\pm 2\%$ tolerance. Other tolerances available are upon request.

These diodes are also available in DO-41 case with the type designation 1N4727...1N4761



Glass case MELF Dimensions in mm LL-41

REEL SPECIFICATION

P/N	PKG	QTY		
ZM4727-MS THRU ZM4761-MS	LL41	5000		

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit			
Power Dissipation	P _{tot}	1 ¹⁾	W			
Junction Temperature	Tj	175	$^{\circ}$			
Storage Temperature Range	T _{stg}	- 65 to + 175	$^{\circ}$			
1) Valid provided that electrodes are kept at ambient temperature.						

Characteristics at T_a = 25℃

Parameter	Symbol	Max.	Unit			
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	170 ¹⁾	K/W			
Forward Voltage at I _F = 200 mA	V _F	1.2	V			
1) Valid provided that electrodes are kept at ambient temperature.						

Characteristics at T_a = 25℃

Туре	Zener Voltage 3)		Dynamic Resistance 1)		Reverse Current		Maximum Surge Current ⁴⁾	Maximum Regulator	
	V_{Zn}	at I _{ZT}	Z _{ZT}	Z _{ZK}	at I _{ZK}	I _R	at V _R	at T _a = 25℃	Current 2)
	(V)	(mA)	Max. (Ω)	Max. (Ω)	(mA)	Max. (µA)	(V)	I _{ZSM} (mA)	I _{ZM} (mA)
ZM4727-MS	3	83	10	400	1	150	1	1375	275
ZM4728-MS	3.3	76	10	400	1	150	1	1375	275
ZM4729-MS	3.6	69	10	400	1	100	1	1260	252
ZM4730-MS	3.9	64	9	400	1	100	1	1190	234
ZM4731-MS	4.3	58	9	400	1	50	1	1070	217
ZM4732-MS	4.7	53	8	500	1	10	1	970	193
ZM4733-MS	5.1	49	7	550	1	10	1	890	178
ZM4734-MS	5.6	45	5	600	1	10	2	810	162
ZM4735-MS	6.2	41	2	700	1	10	3	730	146
ZM4736-MS	6.8	37	3.5	700	1	10	4	660	133
ZM4737-MS	7.5	34	4	700	0.5	10	5	605	121
ZM4738-MS	8.2	31	4.5	700	0.5	10	6	550	110
ZM4739-MS	9.1	28	5	700	0.5	10	7	500	100
ZM4740-MS	10	25	7	700	0.25	10	7.6	454	91
ZM4741-MS	11	23	8	700	0.25	5	8.4	414	83
ZM4742-MS	12	21	9	700	0.25	5	9.1	380	76
ZM4743-MS	13	19	10	700	0.25	5	9.9	344	69
ZM4744-MS	15	17	14	700	0.25	5	11.4	304	61
ZM4745-MS	16	15.5	16	700	0.25	5	12.2	285	57
ZM4746-MS	18	14	20	750	0.25	5	13.7	250	50
ZM4747-MS	20	12.5	22	750	0.25	5	15.2	225	45
ZM4748-MS	22	11.5	23	750	0.25	5	16.7	205	41
ZM4749-MS	24	10.5	25	750	0.25	5	18.2	190	38
ZM4750-MS	27	9.5	35	750	0.25	5	20.6	170	34
ZM4751-MS	30	8.5	40	1000	0.25	5	22.8	150	30
ZM4752-MS	33	7.5	45	1000	0.25	5	25.1	135	27
ZM4753-MS	36	7	50	1000	0.25	5	27.4	125	25
ZM4754-MS	39	6.5	60	1000	0.25	5	29.7	115	23
ZM4755-MS	43	6	70	1500	0.25	5	32.7	110	22
ZM4756-MS	47	5.5	80	1500	0.25	5	35.8	95	19
ZM4757-MS	51	5	95	1500	0.25	5	38.8	90	18
ZM4758-MS	56	4.5	110	2000	0.25	5	42.6	80	16
ZM4759-MS	62	4	125	2000	0.25	5	47.1	70	14
ZM4760-MS	68	3.7	150	2000	0.25	5	51.7	65	13
ZM4761-MS	75	3.3	175	2000	0.25	5	56	60	12

¹⁾ The dynamic resistance is derived from the 60 Hz AC voltage which results when an AC current having an RMS value equal to 10% of the Zener Current (I_{ZT} or I_{ZK}) is superimposed on I_{ZT} or I_{ZK}. Dynamic resistance is measured at two points to insure a sharp knee on the breakdown curve and to eliminate unstable units.

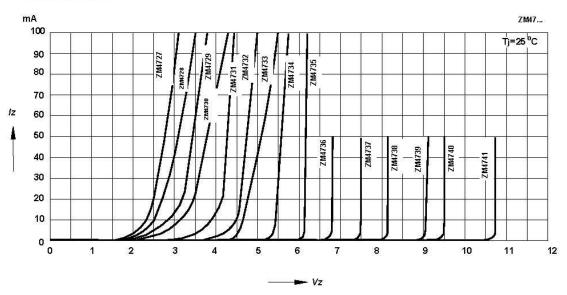
²⁾Valid provided that electrodes are kept at ambient temperature.

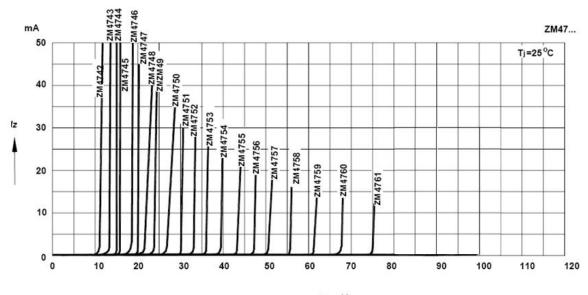
³⁾Tested with pulses tp = 20 ms.

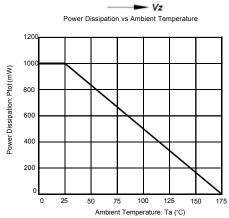
⁴⁾ The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current I_{ZT}.

Breakdowm characteristics

Tj=constant(pulsed)









Semiconductor



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